

## IN THE CLAIMS

Please cancel Claims 1-42 without prejudice or disclaimer of subject matter and add new Claims 43-53 as follows.

1-42. (Cancelled)

43. (New) A method for manufacturing a spacer which defines an interval between substrates opposing each other, comprising steps of:

- forming a first unevenness on a spacer substrate; and
- forming a second unevenness of a smaller cycle period than that of the first unevenness on the spacer substrate on which the first unevenness is formed.

44. (New) A method for manufacturing a spacer which defines an interval between substrates opposing each other, comprising steps of:

- forming a first unevenness on a spacer substrate; and
- forming a second unevenness of a smaller amplitude than that of the first unevenness on the spacer substrate on which the first unevenness is formed.

45. (New) The method according to claim 44 or 45, wherein

- the step of forming the first unevenness is a chemical processing.

46. (New) The method according to claim 45, wherein

- the chemical processing is an anode oxidation process.

47. (New) The method according to claim 43 or 44, wherein the step of forming the second unevenness is non-chemical processing.
48. (New) The method according to claim 47, wherein the non-chemical processing is mechanical processing.
49. (New) The method according to claim 48, wherein the mechanical processing is a grading processing.
50. (New) The method according to claim 43 or 44, further comprising: a step of forming a high resistivity film on the spacer substrate, after the step of forming the second unevenness.
51. (New) A method for manufacturing a spacer which defines an interval between substrates opposing each other, comprising steps of:
- forming on a spacer substrate a fine particle film having an uneven surface; and
- forming a high resistivity film on the spacer substrate on which the fine particle film is formed.

52. (New) The method according to claim 51, wherein  
the step of forming the fine particle film is a process of immersing  
the spacer substrate in a liquid in which a fine particle is dispersed.

53. (New) A method of manufacturing an electron beam generating  
apparatus comprising a first substrate having an electron-emitting element, a target  
irradiated with an electron emitted from the electron-emitting element, a second substrate  
disposed in opposition to the first substrate and a spacer defining an interval between the  
first and second substrates, the method comprising steps of:

forming a spacer; and

disposing the spacer between the first and second substrates,

wherein the step of forming the spacer comprises the steps of:

forming a first unevenness on a spacer substrate; and

forming a second unevenness of a smaller cycle period than  
that of the first unevenness on the spacer substrate on which the first unevenness is formed.

54. (New) A method of manufacturing an electron beam generating  
apparatus comprising a first substrate having an electron-emitting element, a target  
irradiated with an electron emitted from the electron-emitting element, a second substrate  
disposed in opposition to the first substrate and a spacer defining an interval between the  
first and second substrates, the method comprising steps of:

forming a spacer; and  
disposing the spacer between the first and second substrates,  
wherein the step of forming the spacer comprises the steps of:  
forming a first unevenness on a spacer substrate; and  
forming a second unevenness of a smaller amplitude than  
that of the first unevenness on the spacer substrate on which the first unevenness is formed.

55. (New) A method of manufacturing an electron beam generating apparatus comprising a first substrate having an electron-emitting element, a target irradiated with an electron emitted from the electron-emitting element, a second substrate disposed in opposition to the first substrate and a spacer defining an interval between the first and second substrates, the method comprising steps of:

forming a spacer; and  
disposing the spacer between the first and second substrates,  
wherein the step of forming the spacer comprises the steps of:  
forming on a spacer substrate a fine particle film having an  
uneven surface; and  
forming a high resistivity film on the spacer substrate on  
which the fine particle film is formed.